

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A method for manufacturing a solid-state imaging device by ~~sticking~~adhering a transparent substrate, in which ~~plural~~a plurality of frame-shaped spacers are formed, via an adhesive to a wafer on which plural solid-state imaging elements are formed, and by dividing the transparent substrate and the wafer for each solid-state imaging element, each of the solid-state imaging elements on the wafer being surrounded by each of the plurality of spacers, the method comprising the steps of:

~~sticking~~adhering a transfer member, to which the adhesive is applied, to the ~~spacer~~plurality of spacers formed on the transparent substrate;

applying pressure to the transparent substrate and the transfer member, which is adhered to the plurality of spacers formed on the transparent substrate; and

releasing the transfer member from the transparent substrate to transfer the adhesive, which is applied to the transfer member, ~~on~~ from the transfer member onto the ~~spacer~~ plurality of spacers formed on the transparent substrate.

2. (original): The method according to claim 1, wherein the transfer member is a rigid body.

3. (original): The method according to claim 2, wherein the transfer member is a glass plate.
4. (original): The method according to claim 1, wherein the transfer member is an elastic body.
5. (original): The method according to claim 4, wherein the transfer member is a flexible plastic film.
6. (original): The method according to claim 5, wherein the transfer member is peeled off such that the angle between the transfer member and the transparent substrate is kept constant.
7. (original): The method according to claim 1, further comprising the step of forming a ridge pattern or a recess pattern in the transfer member, the ridge pattern or the recess pattern being the same pattern as the spacers in the transparent substrate.
8. (original): The method according to claim 1, further comprising the step of applying a release agent on the surface of the transfer member.
9. (original): The method according to claim 8, wherein the release agent is silicon.

10. (original): The method according to claim 1, further comprising the step of carrying out surface modification to the surface of the spacer to which the adhesive is applied.

11. (original): The method according to claim 1, wherein the viscosity of the adhesive is 0.1 Pa·S or more when the adhesive is applied to the transfer member.

12. (original): The method according to claim 1, wherein the adhesive is applied to the transfer member by bar coating, blade coating or spin coating.

13. (original): The method according to claim 1, wherein pressure is applied to the transfer member and the transparent substrate by air pressure or roller pressure.

14. (original): The method according to claim 1, wherein the viscosity of the adhesive is 100 Pa·S to 10000 Pa·S when the adhesive is transferred to the spacer from the transfer member.

15. (original): The method according to claim 1, wherein the adhesive has the thickness from 0.5 μ m to 5.0 μ m after the adhesive is activated.

16. (original): The method according to claim 1, wherein the spacer is bonded to the wafer over the surface to which the adhesive is applied.

17. (withdrawn): A solid-state imaging device manufactured by the method according to claim 1.

18. (withdrawn): The solid-state imaging device according to claim 17, wherein the solid-state imaging element and the inner surface of the spacer are separated by 50 μ m to 100 μ m over the whole edge of the solid-state imaging element.

19. (withdrawn): The solid-state imaging device according to claim 17, wherein the width of the spacer is 100 μ m to 500 μ m.

20. (withdrawn): The solid-state imaging device according to claim 17, wherein chamfer edges are formed in the surface of the spacer to which the adhesive is applied, the surplus adhesive is contained in the space between the wafer and the chamfer edges.

21. (withdrawn): A solid-state imaging device that comprises a solid-state imaging element on a chip wafer, a frame-shaped spacer bounded on the chip wafer via an adhesive, and a transparent plate on the spacer to seal the solid-state imaging element, the solid-state imaging element being surrounded by the spacer;

wherein the solid-state imaging element and the inner surface of the spacer are separated by 50 μ m to 100 μ m over the whole edge of the solid-state imaging element.

22. (withdrawn): A solid-state imaging device that comprises a solid-state imaging element on a chip wafer, a frame-shaped spacer bounded on the chip wafer via an adhesive, and a transparent plate on the spacer to seal the solid-state imaging element, the solid-state imaging element being surrounded by the spacer;

wherein the width of the spacer is 100 μ m to 500 μ m.

23. (new): The method according to claim 1, further comprising the step of bonding the wafer to the transparent substrate by pressing the wafer and the plurality of spacers formed on the transparent substrate, wherein the adhesive transferred from the transfer member onto the plurality of spacers bonds the plurality of spacers to the wafer.